

Webinar

Rad-hard low-noise linear
regulator for high-performance
satellite sensing and
communications systems

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Agenda

- Subsystems with low-noise power supply requirements
- Noise and PSRR basics
- Measuring noise & PSRR in low-noise power supplies
- TPS7H1111 introduction
- TPS7H1111 noise & PSRR
- TPS7H1111 final results

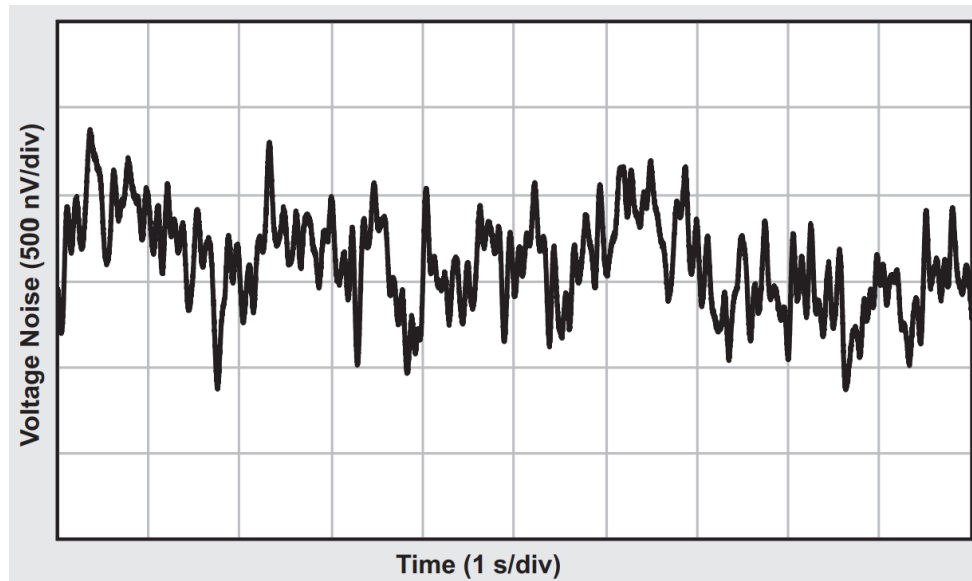
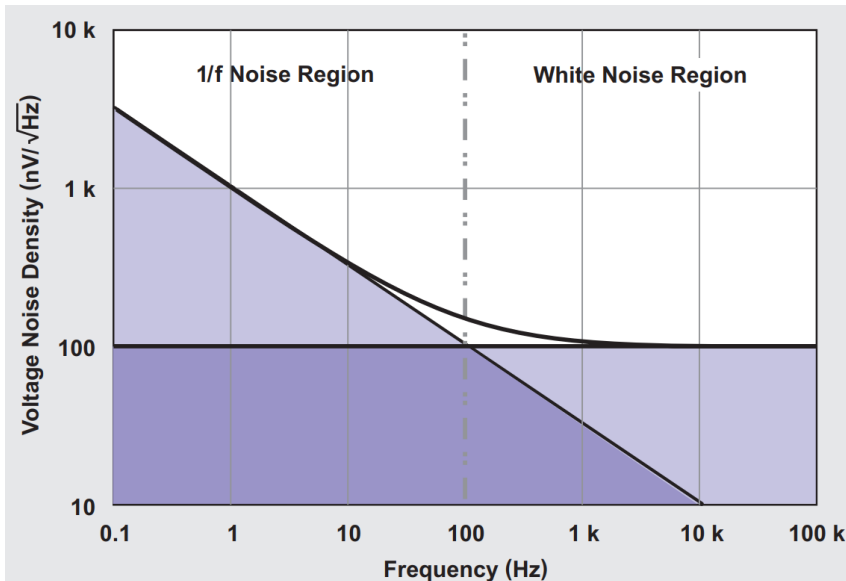
Subsystems with Low-Noise requirements

- As satellites process more data, signal processing requirements continue increasing
- Without careful power supply design, the power can become a limiting factor for:
 - Analog to digital converters (ADCs)
 - Digital to analog converters (DACs)
 - Imaging sensors
 - Clocking circuits
- A high-performance ADC is a key IC that may benefit from an ultra-low noise LDO
 - Noise can couple to an ADC both directly and through its clock mixing path
 - This coupling can reduce the SFDR (spurious free dynamic range) of the ADC



Noise & PSRR basics | Noise

- All electrical devices create inherent noise
 - The most problematic noise to filter out is generally low frequency output noise (also referred to as $1/f$ noise or flicker noise)
 - Discrete filters would require large component values and consume valuable board space



Noise & PSRR basics | PSRR

- Linear regulators are often powered by switching regulators which inherently generate ripple voltage at the switching frequency and harmonics of higher frequency.
 - This input noise is attenuated by the Power Supply Rejection Ratio (PSRR) of the linear regulator before being passed to the linear regulator output.
 - $PSRR = 20 \times \log_{10} \frac{V_{IN}}{V_{OUT}}$



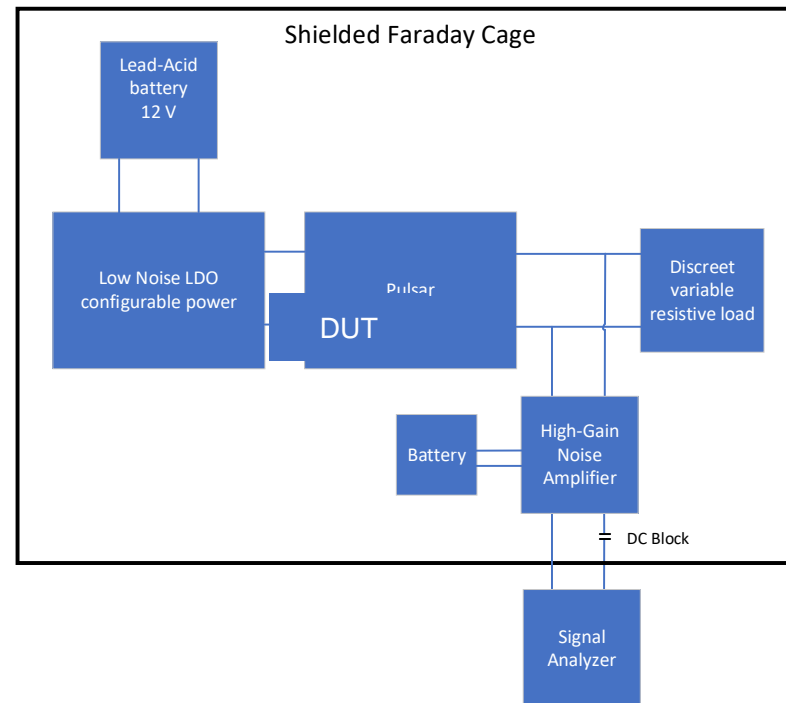
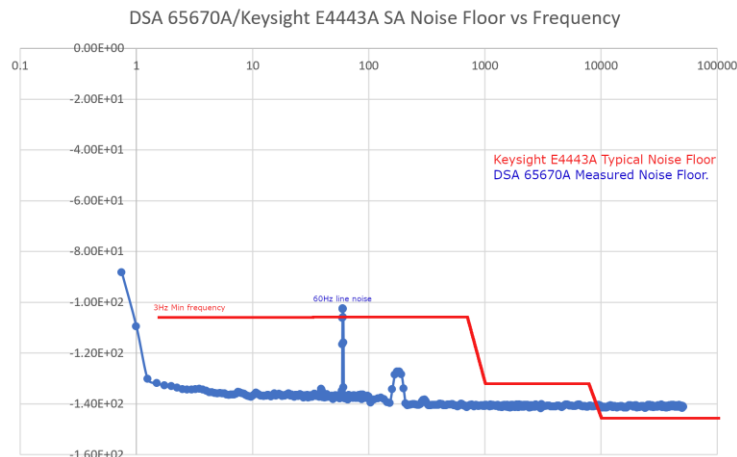
Example of 100 mV being attenuated by 40 dB

Measuring noise & PSRR | Noise

- Noise spectral density is obtained by sampling the random noise for a period of time
- External sources of noise must be removed which requires:
 - EMI shielding (Faraday cage)
 - Careful layout to minimize antennas or ground loops
 - Removing as much noise as possible from the input power supply
- Additional considerations:
 - Very large output AC signal capacitor to facilitate low frequency testing
 - Low noise, high gain pre-amplifier to gain up noise to a level that the signal analyzer can measure

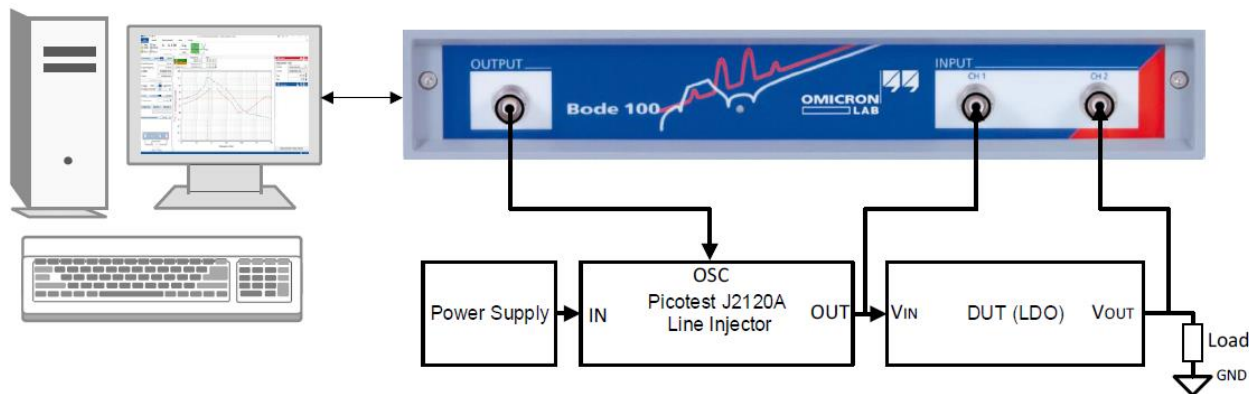
Measuring noise & PSRR | Noise

- Setup shown to right
- Signal analyzer options considered
 - HP DSA 35670A
 - Keysight E4443A



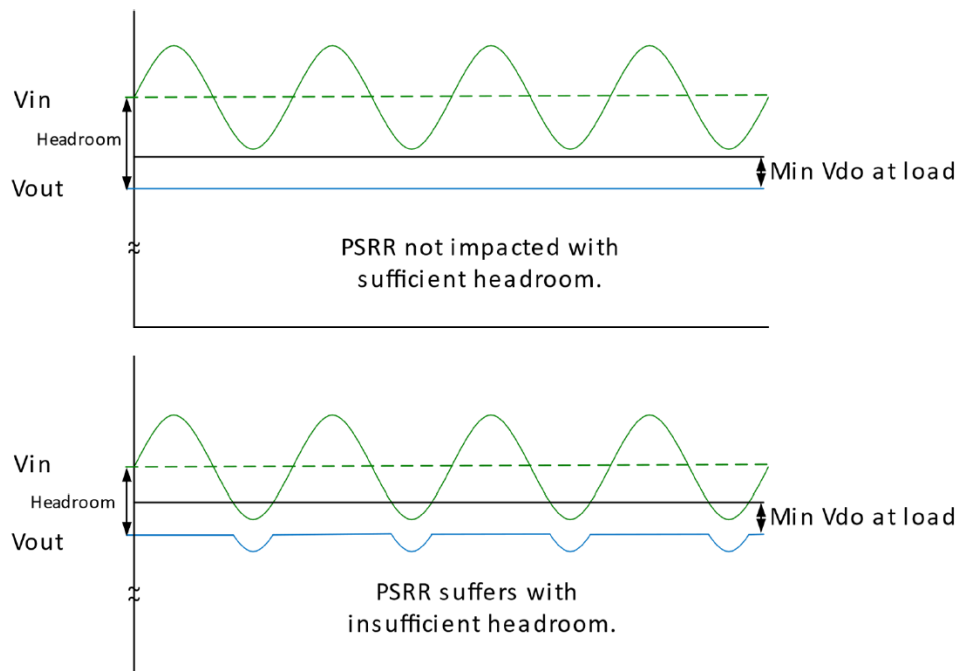
Measuring noise & PSRR | PSRR

- A voltage ripple is injected on VIN and the attenuated VOUT ripple is then measured
 - To properly drive VIN, the LDO's input capacitance is removed
- An Omicron Bode 100 and Picotest J2120A can be utilized



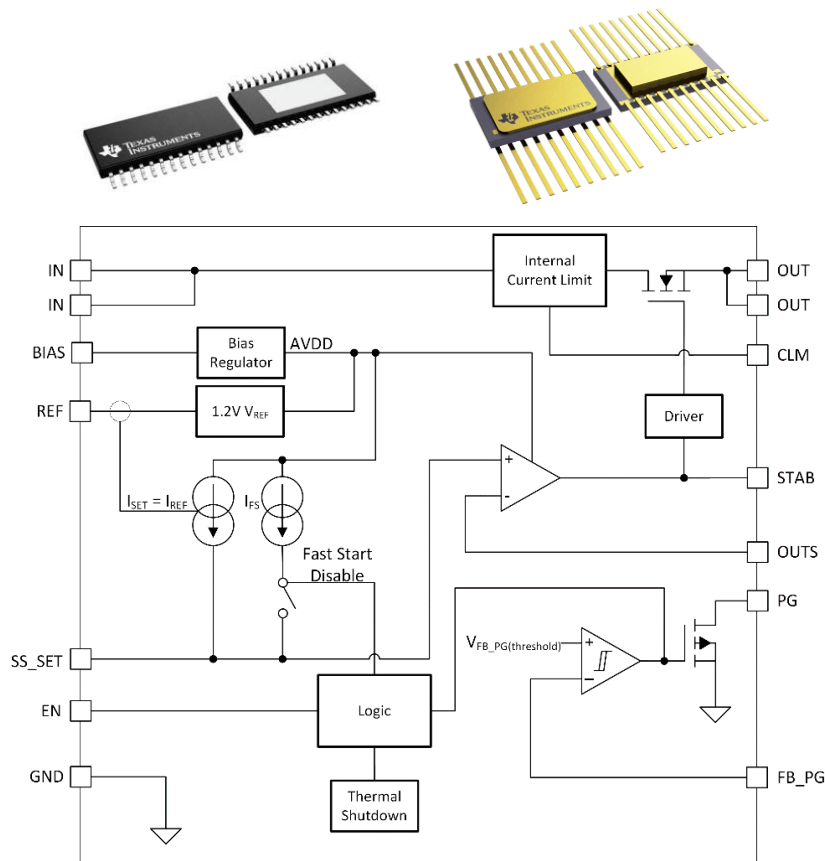
Measuring noise & PSRR | PSRR

- Sufficient headroom is required for the test
- The injected signal needs to be large enough to be measured at the output but small enough to be considered small signal from the LDOs perspective



TPS7H1111 | Overview

- Linear regulator with architecture optimized for low noise and high PSRR
- TID up to 100 krad(Si) and SEL/SEB/SEGR immune to 75 MeV-cm²/mg
- Electrical
 - Input voltage, V_{IN} : 0.85V to 7V
 - Bias supply, V_{BIAS} : 2.2V to 14V
 - Output voltage, V_{OUT} : 0.4V to 5.5V
 - Output current, I_{OUT} : 1.5A
 - Dropout voltage, V_{DO} : 450 mV (max) at 1.5 A
- Features
 - -1.3% to +1.2% accuracy across line, load, and temperature
 - Ability to parallel multiple devices
 - Configurable power good threshold (FB_PG)
 - Configurable current limit behavior (CLM)
 - Enable pin (EN)
 - Noise reduction and soft start pin (SS_SET)
 - Remote sense (OUTS)



TI Space product grades

Same radiation levels, same qualification, different package



Pin-to-pin compatible, different radiation levels

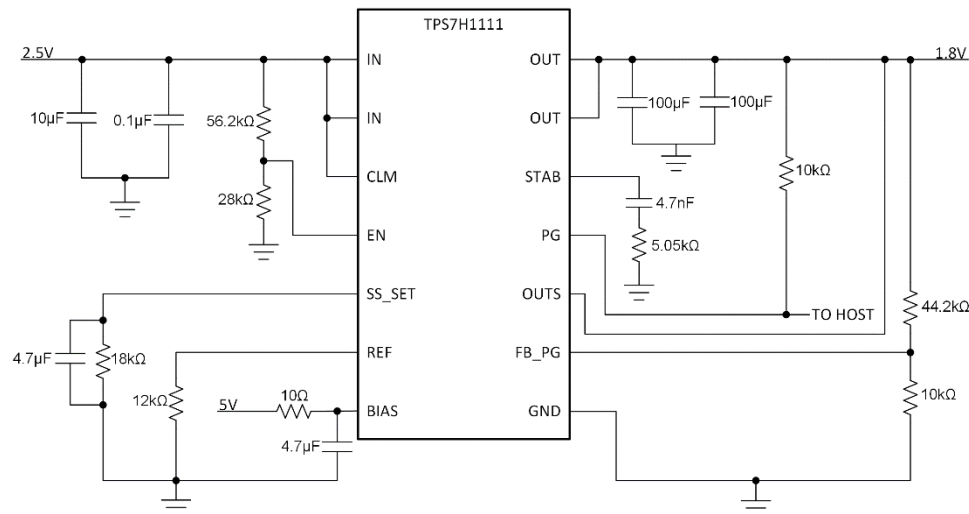
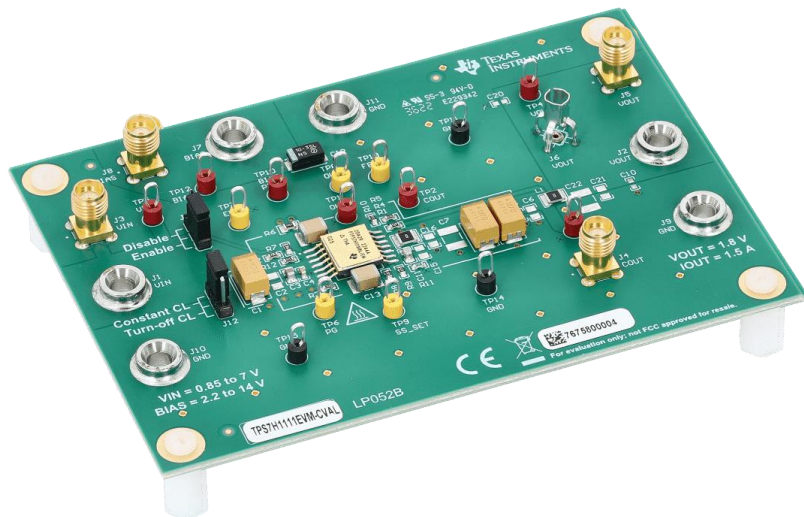
Packaging	Plastic	Plastic	Ceramic / Metal Can
Mil. Spec	VID	SMD	SMD
Burn- in	No	Yes	Yes
TID Char	30 – 50 krad(Si)	<----- 50krad(Si) – 300 krad(Si) ----->	
TID RLAT	20, 30, or 50 krad(Si)	<----- Non-RHA, 50, 100, or 300 krad(Si) ----->	
SEL	43 MeV·cm ² /mg	<----- ≥ 60 MeV·cm ² /mg ----->	

TPS7H1111-SEP

TPS7H1111-SP

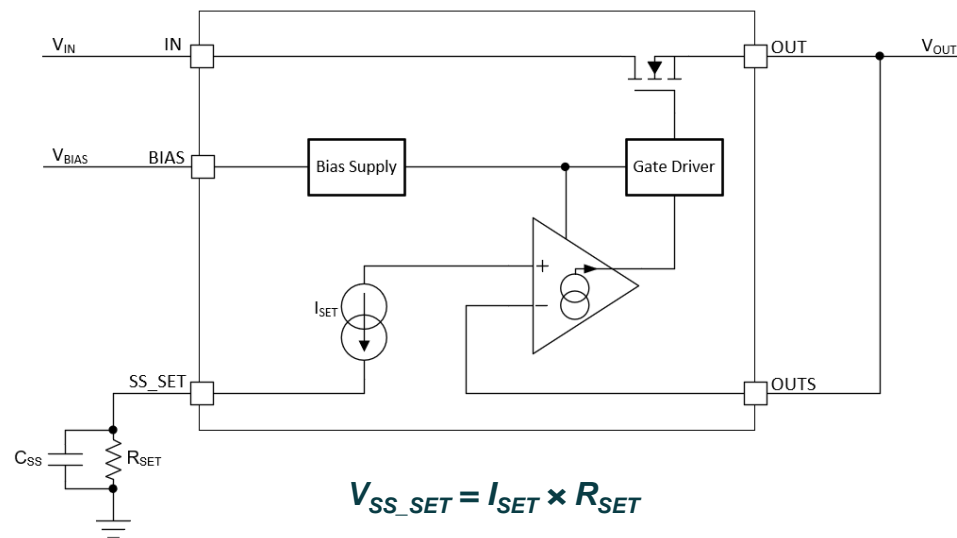
TPS7H1111 noise & PSRR | Hardware overview

- Most measurements taken on TI evaluation board
- Focus on a golden configuration of 2.5V input, 1.8V output, with 5V bias supply

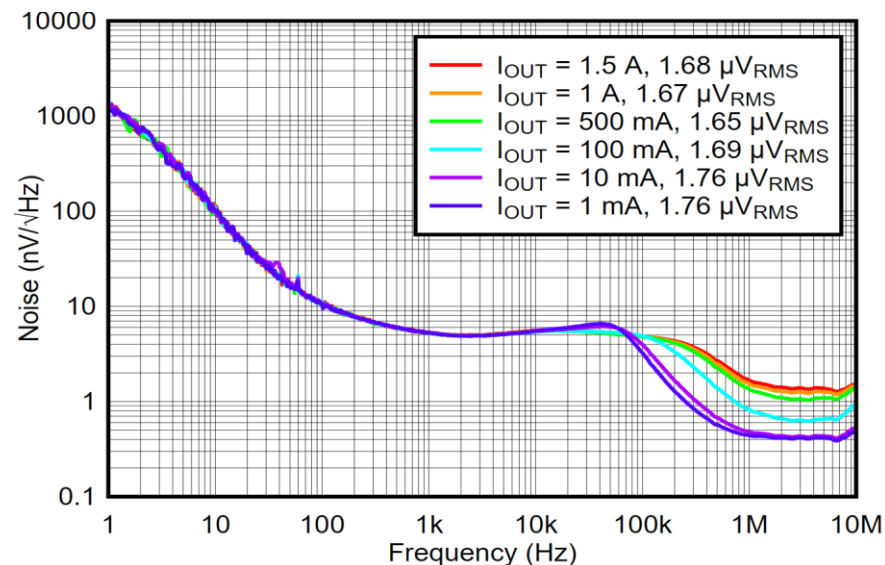
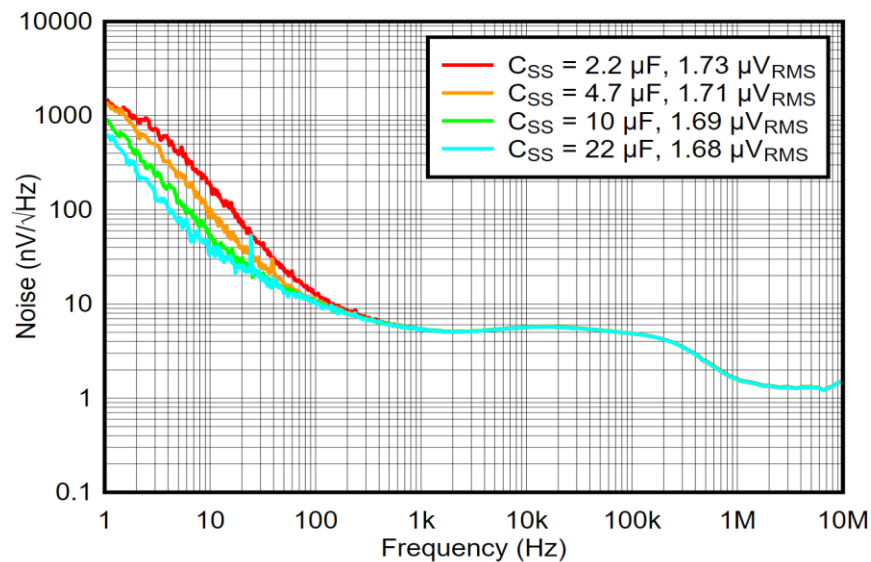


TPS7H1111 noise & PSRR | Noise optimization

- A low-noise optimized, unity gain error amplifier is utilized to configure the output voltage
- A precision 100μA is sourced from the SS_SET pin
 - R_{SET} sets the output voltage
 - The desired output voltage is generated on SS_SET
 - The voltage on SS_SET will be replicated on the output
- Noise on SS_SET is not gained up by the resistor divider ratio (as in a traditional LDO)
- The SS_SET voltage is heavily filtered by C_{SS}
- The C_{SS} capacitor also enables a controllable soft start time



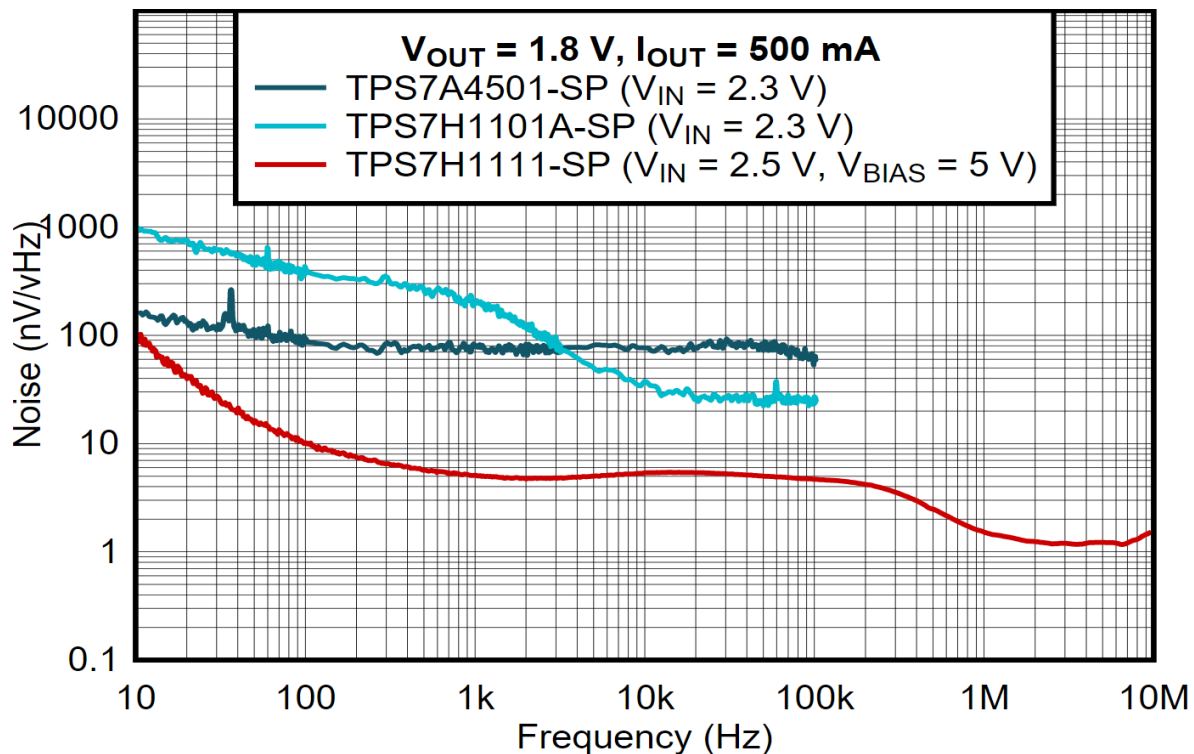
TPS7H1111 noise & PSRR | Noise results



$$V_{IN} = 2.5V, V_{BIAS} = 5V, V_{OUT} = 1.8V$$

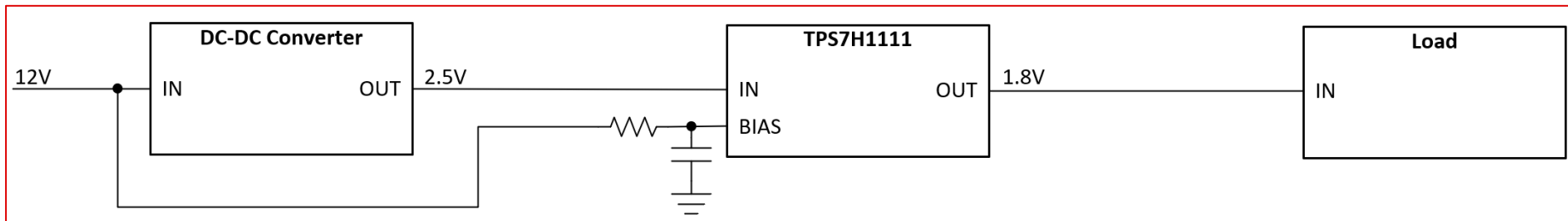
TPS7H1111 noise & PSRR | Noise comparison

Comparison to existing TI devices

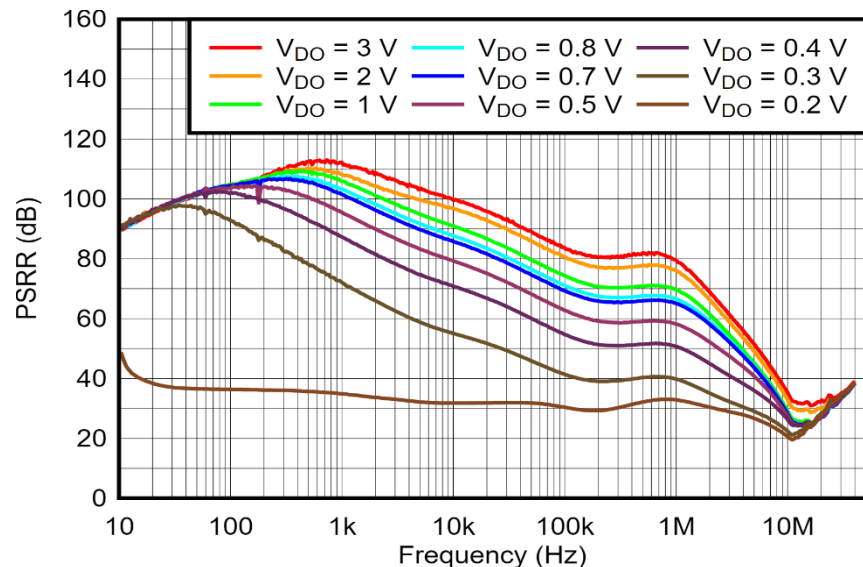


TPS7H1111 noise & PSRR | PSRR optimization

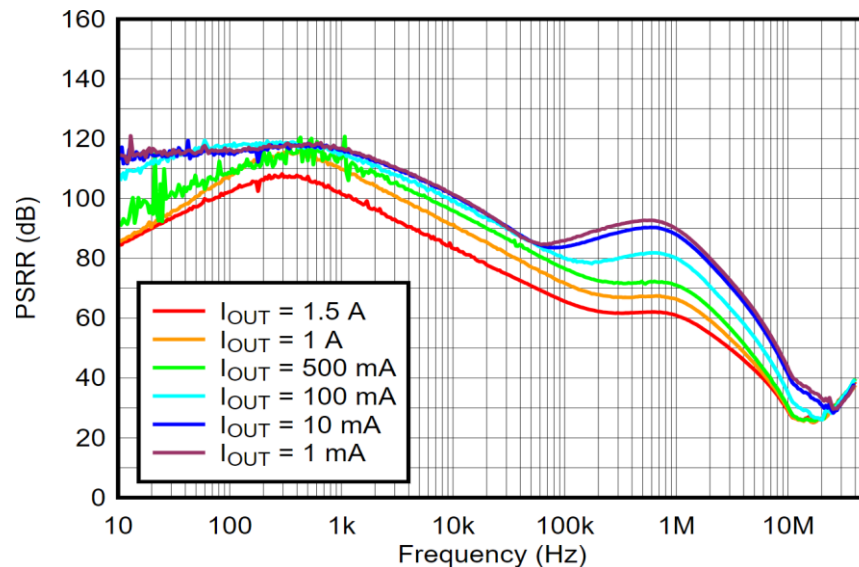
- High bandwidth error amplifier
 - Ability to maintain high gain through a wide frequency range attenuates input noise across a wide frequency
 - Must ensure stability across this bandwidth
- Pass element optimization
 - High self-gain required to maximize PSRR
 - An NMOS device has higher self-gain than a similar PMOS and therefore an NMOS was selected
 - Compared to a PMOS, an NMOS requires either a high dropout voltage requirement or a separate voltage greater than V_{OUT} to drive the NMOS gate
 - Charge pump could be utilized but this may introduce extra noise
 - Bias rail included, low current enables additional RC filtering to maximize overall PSRR



TPS7H1111 noise & PSRR | PSRR results



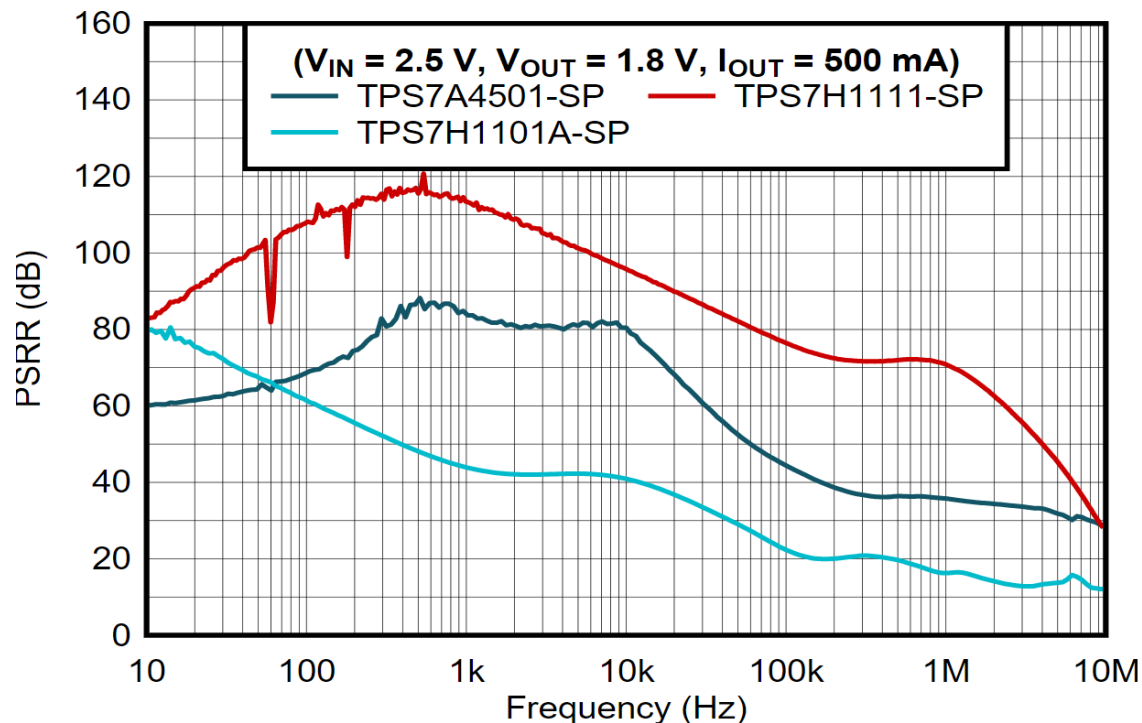
$$V_{IN} = V_{OUT} + V_{DO}, V_{BIAS} = V_{OUT} + 1.6V, V_{OUT} = 1.8V$$



$$V_{IN} = 2.5V, V_{BIAS} = 5V, V_{OUT} = 1.8V$$

TPS7H1111 noise & PSRR | PSRR comparison

Comparison to existing TI devices



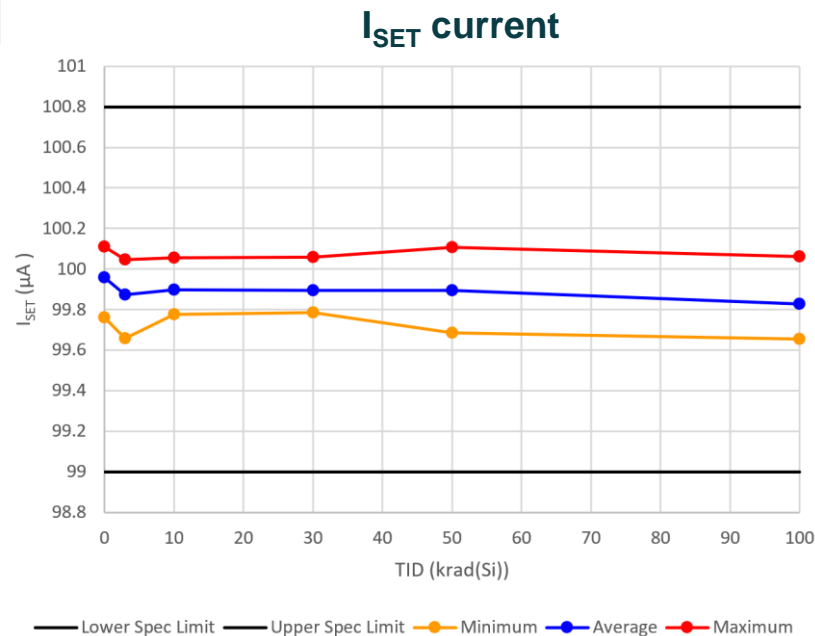
TPS7H1111 noise & PSRR | PSRR and noise

The TPS7H1111 offers many benefits while a discrete filter may be ineffective or impractical

Filter Type	Filter Values	Benefits	Tradeoffs
LC Filter with 5 kHz cutoff	10 μ H and 100 μ F	<ul style="list-style-type: none">Reduces high frequency ripple	<ul style="list-style-type: none">Affects control loopSlower response to load transientsNo 1/f noise filtering
LC Filter with 10 Hz cutoff	10mH and 25mF	<ul style="list-style-type: none">Reduces high frequency ripple1/f noise filtering	<ul style="list-style-type: none">Affects control loopSlower response to load transientsImpractical size
TPS7H1111	N/A	<ul style="list-style-type: none">Reduces high frequency ripple1/f noise filteringImproved transient performance	<ul style="list-style-type: none">Active component required

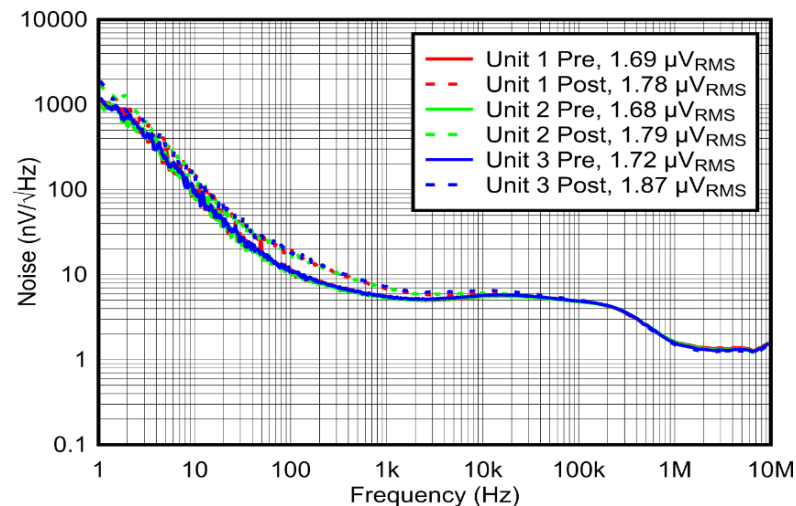
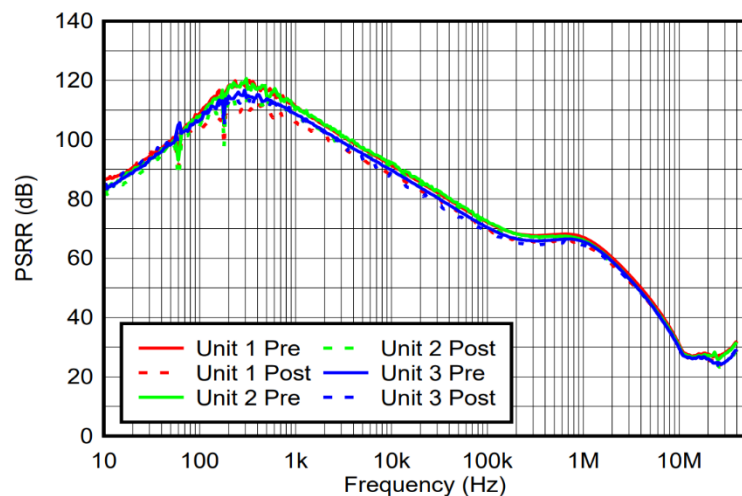
TPS7H1111 | TID overview

- The TPS7H1111 is designed and characterized to a TID of 100krad(Si).
 - Samples were irradiated then tested using the ATE (automated test equipment) program
- The TPS7H1111 is tested under both HDR and LDR conditions
 - HDR on biased and unbiased devices using TI's Co-60 gamma cell
 - LDR
 - The LBC7 process with annular NMOS has been demonstrated to be ELDRs free
 - An LDR characterization was performed to 100 krad(Si)



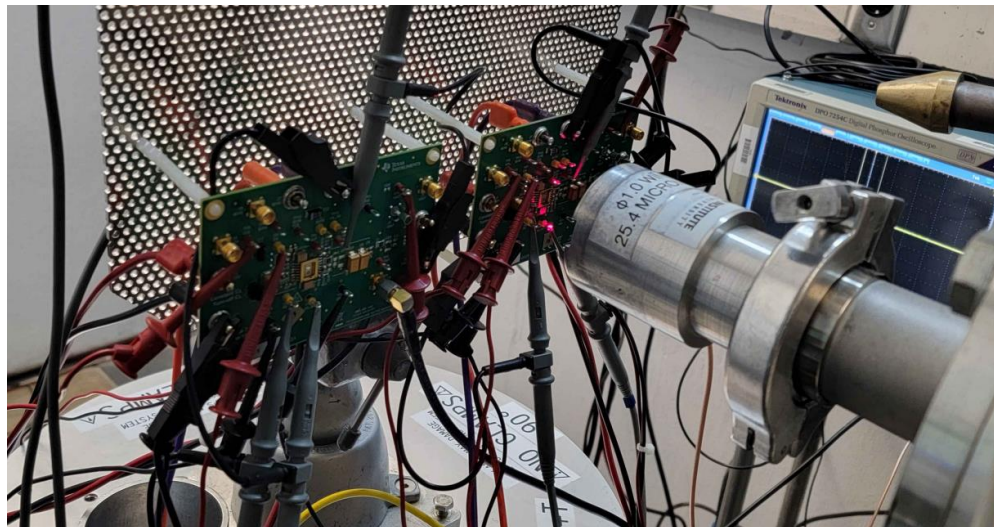
TPS7H1111 | TID for noise and PSRR

- Traditionally only ATE testing is performed post TID
- Additional post-TID noise and PSRR testing was done on an EVM for the TPS7H1111 due to the importance of the spec for this device
- Minimal change was observed



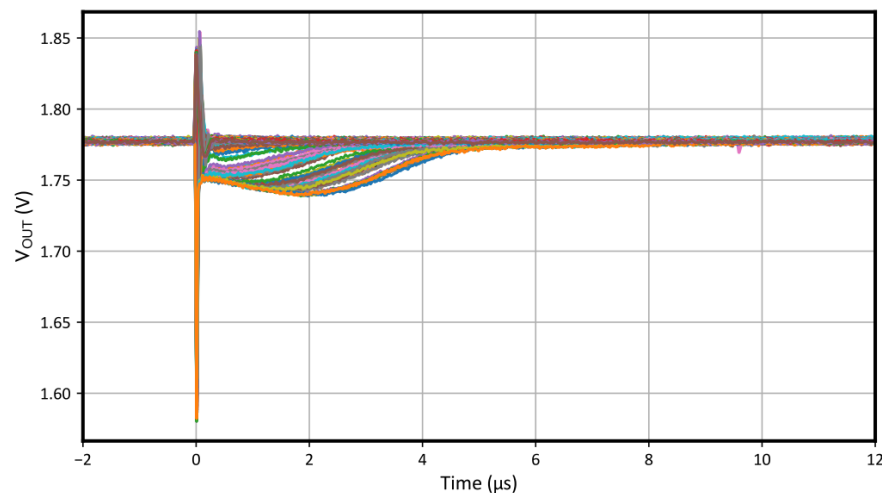
TPS7H1111 | SEE overview

- Tested at Texas A&M Cyclotron Institute's Radiation Effects Facility
- DSEE testing performed with $V_{IN} = 7V$ and $V_{BIAS} = 14V$ using ^{165}Ho
 - SEL testing was performed at a die temperature of approximately 125°C
 - SEB and SEGR testing was performed at a die temperature of approximately 25°C
 - SEB was tested with both the device enabled and with the device disabled.
- Four devices were tested for SEL and SEB/SEGR
 - No DSEE events were observed



TPS7H1111 | SEE – SETs

- SET testing performed with $V_{IN} = 2.5V$, $V_{BIAS} = 5V$, $V_{OUT} = 1.8V$, and $I_{OUT} = 1.5A$
 - Both ^{165}Ho and ^{109}Ag were utilized for an LET range of 48 to $75\text{MeV}\times\text{cm}^2/\text{mg}$
- The TPS7H1111 was found to have a very low SET cross section
 - The LET onset threshold in this configuration was found to be $60\text{MeV}\times\text{cm}^2/\text{mg}$
 - No SEFIs were recorded
- Event rate calculations were performed*
 - LEO (Low-Earth Orbit) MTBE of 1.51×10^6 years
 - GEO (Geosynchronous-Earth Orbit) MTBE of 5.09×10^5 years

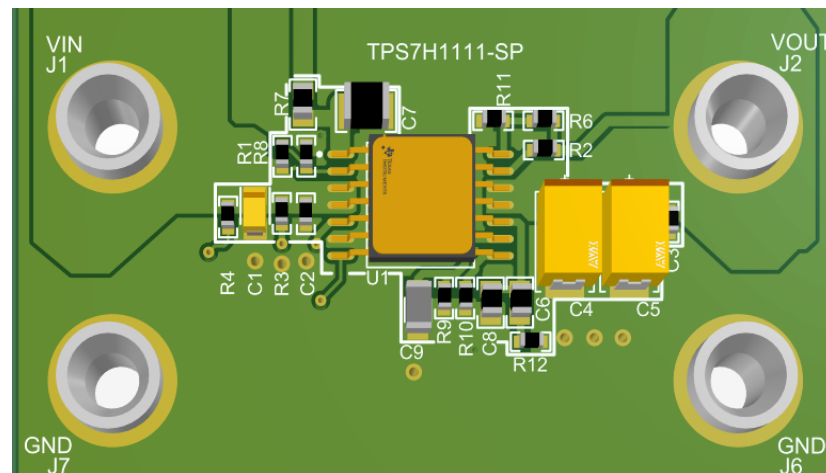


SETs detected for a single run (41 SET events with V_{OUT} transients $\geq 5\%$)

*Using CREME96 orbital integral flux estimations, 2.54 mm (100 mil) aluminum shielding, and “worst-week” solar activity

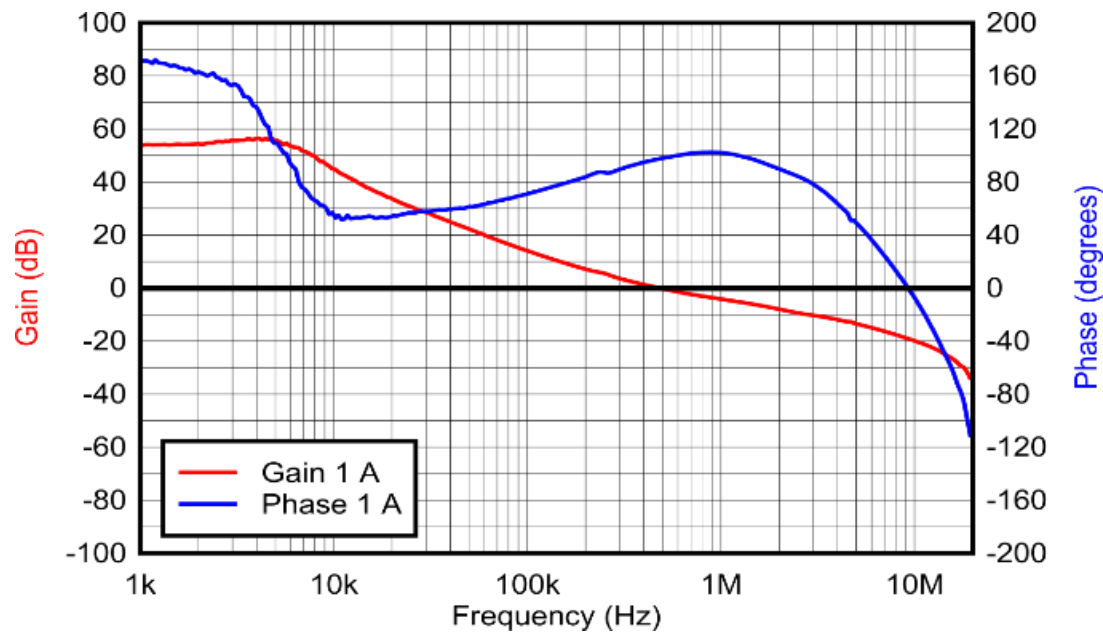
TPS7H1111 | Other benefits

- Excellent output voltage accuracy of -1.3% to 1.2%
 - Applies across -55°C to 125°C , a wide range of currents, input voltages, and output voltages
 - Simplifies powering circuits with tight voltage supply requirements
- Open drain power good pin with an adjustable power good threshold
 - Enables flexible sequencing options and voltage monitoring
- Configurable current limit for improved fault management
 - Turn-off current limit mode: The regulator turns off to prevent sustained high-power dissipation
 - Brick-wall current limit mode: The regulator maintains constant output current until fault is removed



TPS7H1111 | Stability

Bode plot from 2x100 μF AVX capacitors (TBME107K020LBLC9045)

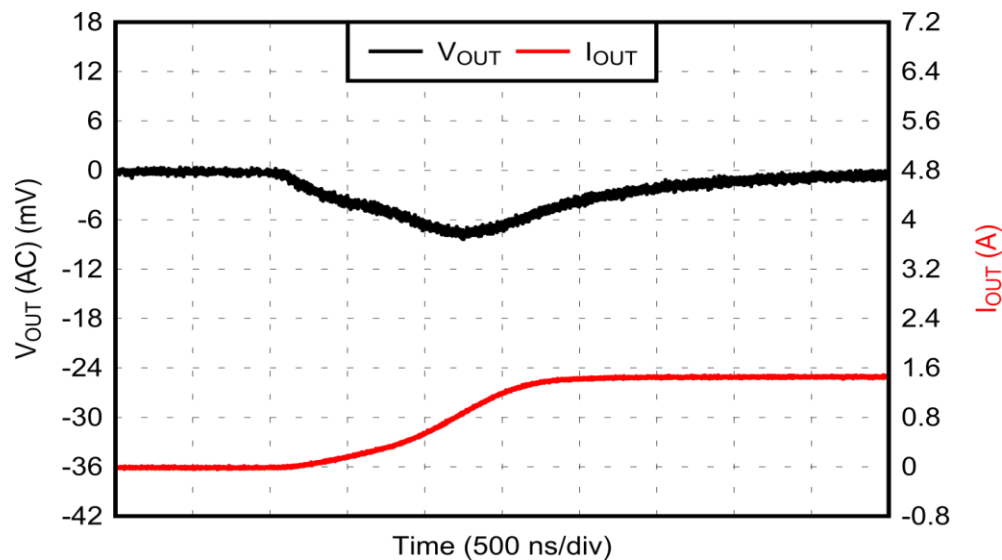


Load Current	Results	
	Phase Margin	Gain Margin
0A	83°	29dB
1A	98°	19dB
1.5A	99°	19dB

$$V_{IN} = 2.5V, V_{BIAS} = 5V, V_{OUT} = 1.8V$$

TPS7H1111 | Stability

- Demonstrated large signal stability with a fast load step
 - 1mA to 1.5A load step at a slew rate of 0.8A/ μ s.
- The output voltage falls appropriately 8mV which is 0.4% of the nominal output voltage.
- Smoothly recovers within approximately 3.5 μ s.



TPS7H1111 | Getting started

You can start evaluating this device leveraging the following:

Content type	Content title	Link to content or more details
Radiation Reports	TPS7H1111-SP Technical Documentation TPS7H1111-SEP Technical Documentation	https://www.ti.com/product/TPS7H1111-SP#tech-docs https://www.ti.com/product/TPS7H1111-SEP#tech-docs
EVM	TPS7H1111EVM-CVAL (Ceramic) TPS7H1111EVM (Plastic)	https://www.ti.com/tool/TPS7H1111EVM-CVAL https://www.ti.com/tool/TPS7H1111EVM
Simulation Model	TPS7H1111-SP PSpice Model	https://www.ti.com/product/TPS7H1111-SP#design-tools-simulation

References

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- *Space engineering Electrical and electronic*, ECSS-E-ST-20C Rev.2, European Cooperation for Space Standardization, April 2022. [Online]. Available: <https://ecss.nl/standard/ecss-e-st-20c-rev-2-electrical-and-electronic-8-april-2022/>
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- J. C. Colon, H. Torres, J. Valle and V. Narayanan, "Radiation Evaluation of the Texas Instruments TPS7H2201-SP eFuse," 2019 IEEE Radiation Effects Data Workshop, San Antonio, TX, USA, 2019, pp. 1-5, doi: 10.1109/REDW.2019.8906601.
- "TPS7H1111-SP total ionizing dose (TID) radiation report," Texas Instruments, Dallas, Texas, Accessed June 5, 2023. [Online]. Available: <https://www.ti.com/lit/pdf/SLVK126>
- "TPS7H1111-SP Single-Event Effects (SEE) radiation report," Texas Instruments, Dallas, Texas, Accessed: June 5, 2023. [Online]. Available: <https://www.ti.com/lit/pdf/SLVK128>
- Neu, Thomas. "Designing a modern power supply for RF sampling converters," Texas Instruments, Dallas, Texas, Accessed: May 30, 2023. [Online]. Available: <https://www.ti.com/lit/pdf/SLYT720>
- <https://www.ti.com/lit/an/slyt583/slyt583.pdf>
- Special thanks to all current and former members of the Space Power team who made this product possible, especially Wade Vonbergen, Tyler Lew, Kashif Haq, Tony Owens, Josh Cortman, Hector Torres, Aaron Chen, Justin Nuttall, Larry Gewax, Anthony Marinelarena, Tim Duryea, and Patrick Joseph.



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